

CD42__40B, CD47__40B
Dual SCR/Diode Isolated
POW-R-BLOK™ Module
40 Amperes / Up to 1800 Volts

Description:

Powerex SCR/Diode Modules are designed for use in applications requiring phase control and isolated packaging. The modules are isolated for easy mounting with other components on a common heatsink. *POW-R-BLOK™* has been tested and recognized by the Underwriters Laboratories.

Features:

- Electrically Isolated Heatsinking
- DBC Alumina (Al₂O₃) Insulator
- Copper Baseplate
- Low Thermal Impedance for Improved Current Capability
- UL Recognized (E78240)

Benefits:

- No Additional Insulation Components Required
- Easy Installation
- No Clamping Components Required
- Reduce Engineering Time

Applications:

- Bridge Circuits
- AC & DC Motor Drives
- Battery Supplies
- Power Supplies
- Large IGBT Circuit Front Ends
- Lighting Control
- Heat & Temperature Control
- Welders

CD42, CD47 Outline Dimensions

Dimension	Inches	Millimeters
A	3.66	93
B	0.79	20
C	3.15	80
D	1.18	30
F	0.61	15.5
G	0.79	20
H	0.79	20
J	0.16	4
K	0.22	5.7
L	0.59	15
M	1.10	28
N	0.31	8
P	0.94	24
Q	1.16	29.4
S	0.11 x .03	2.8 x 0.8
T	0.25	6.4
U	M5	M5

Note: Dimensions are for reference only.

Ordering Information:

Select the complete nine digit module part number from the table below. Example: CD421640B is a 1600Volt, 40 Ampere Dual SCR/Diode Isolated *POW-R-BLOK™* Module

Type	Voltage Volts (x100)	Current Amperes	Version
CD42	08	40	B
CD47	12		
	14		
	16		
	18		

Absolute Maximum Ratings

Characteristics	Conditions	Symbol	Units
Repetitive Peak Forward and Reverse Blocking Voltage		V_{DRM} & V_{RRM}	up to 1800 V
Non-Repetitive Peak Reverse Blocking Voltage ($t < 5$ msec)		V_{RSM}	$V_{RRM} + 100$ V
RMS Forward Current	180° Conduction, $T_C=85^\circ\text{C}$	$I_{T(RMS)}$	63 A
Average Forward Current	180° Conduction, $T_C=85^\circ\text{C}$	$I_{T(AV)}$	40 A
Peak One Cycle Surge Current, Non-Repetitive	60 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I_{TSM}	750 A
	60 Hz, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I_{TSM}	890 A
	60 Hz, No V_{RRM} reapplied, $T_j=25^\circ\text{C}$	I_{TSM}	985 A
	50 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I_{TSM}	715 A
	50 Hz, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I_{TSM}	850 A
	50 Hz, No V_{RRM} reapplied, $T_j=25^\circ\text{C}$	I_{TSM}	940 A
I^2t for Fusing for One Cycle, 8.3 milliseconds	8.3 ms, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I^2t	2,330 A^2sec
	8.3 ms, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I^2t	3,300 A^2sec
	8.3 ms, No V_{RRM} reapplied, $T_j=25^\circ\text{C}$	I^2t	4,030 A^2sec
	10 ms, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I^2t	2,560 A^2sec
	10 ms, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$	I^2t	3,610 A^2sec
	10 ms, No V_{RRM} reapplied, $T_j=25^\circ\text{C}$	I^2t	4,420 A^2sec
Maximum Rate-of-Rise of On-State Current, (Non-Repetitive)	$T_j=125^\circ\text{C}$	di/dt	150 A/ μs
Operating Temperature		T_j	-40 to +125 °C
Storage Temperature		T_{stg}	-40 to +125 °C
Max. Mounting Torque, M5 Mounting Screw on Terminals			25 in.-Lb.
			3 Nm
Max. Mounting Torque, Module to Heatsink			44 in.-Lb.
			5 Nm
Module Weight, Typical			95 g
			3.35 oz.
V Isolation @ 25C	50 – 60 Hz, 1 minute	V_{rms}	3000 V
Circuit to base, all terminals shorted together	50 – 60 Hz, 1 second	V_{rms}	3500 V

Information presented is based upon manufacturers testing and projected capabilities.
 This information is subject to change without notice.
 The manufacturer makes no claim as to the suitability of use, reliability, capability,
 or future availability of this product.

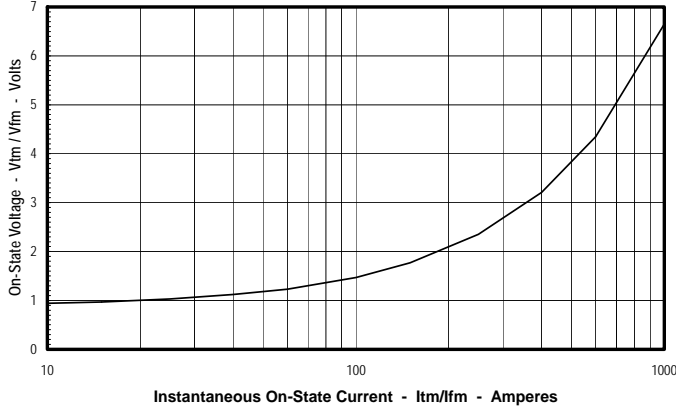
Electrical Characteristics, T_J=25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Max.	Units
Repetitive Peak Forward Leakage Current	I _{DRM}	Up to 1800V, T _J =125°C		20	mA
Repetitive Peak Reverse Leakage Current	I _{RDM}	Up to 1800V, T _J =125°C		20	mA
Peak On-State Voltage	V _{TM} / V _{FM}	I _{TM} / I _{FM} = 200A		1.95	V
Threshold Voltage, Low-level	V _{(TO)1}	T _J = 125°C, I = 16.7% x πI _{T(AV)} to πI _{T(AV)}		1.0	V
Slope Resistance, Low-level	r _{T1}			4.5	mΩ
Minimum dV/dt	dV/dt	T _J =125°C, Up to 800V T _J =125°C, 1200V – 1800V	500 1000		V/μs V/μs
Turn-Off Time (Typical)	t _{off}	T _J = 125°C	40 - 100	(Typical)	μs
Gate Trigger Current	I _{GT}	T _J = 25°C, V _D =6V, Resistive Load		150	mA
Gate Trigger Voltage	V _{GT}	T _J = 25°C, V _D =6V, Resistive Load		3.0	Volts
Non-Triggering Gate Voltage	V _{GDM}	T _J =125°C, V _D =V _{DRM}		0.25	Volts
Non-Triggering Gate Current	I _{GDM}	T _J =125°C, V _D =V _{DRM}		6	mA
Holding Current	I _H	T _J = 25°C		150	mA
Latching Current	I _L	T _J = 25°C		300	mA

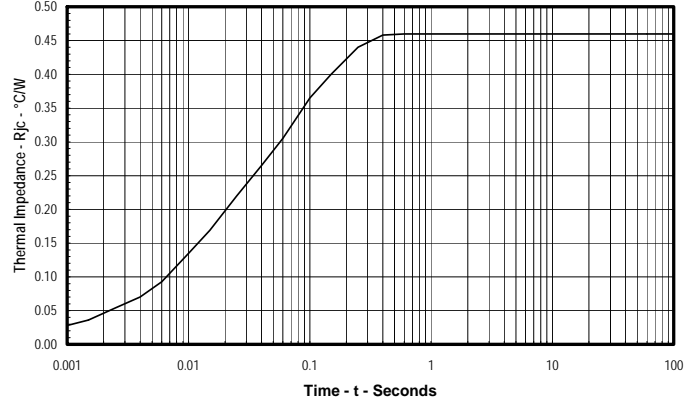
Thermal Characteristics

Characteristics	Symbol		Max.	Units
Thermal Resistance, Junction to Case	R _{ΘJ-C}	Per Module, both conducting	0.33	°C/W
DC Operation		Per Junction, both conducting	0.65	°C/W
Thermal Resistance, Case to Sink Lubricated	R _{ΘC-S}	Per Module	0.1	°C/W

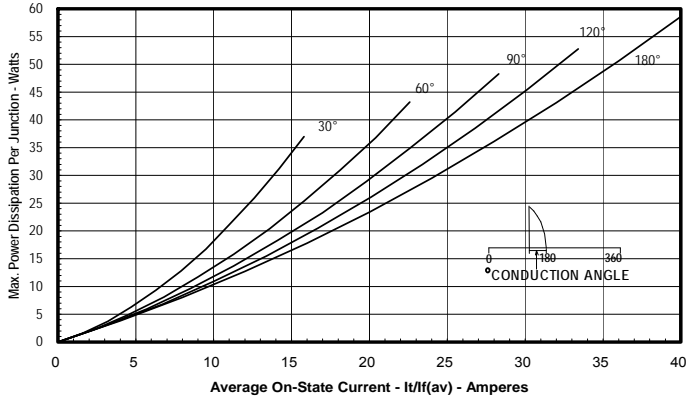
Maximum On-State Forward Voltage Drop
($T_j = 125^\circ\text{C}$)



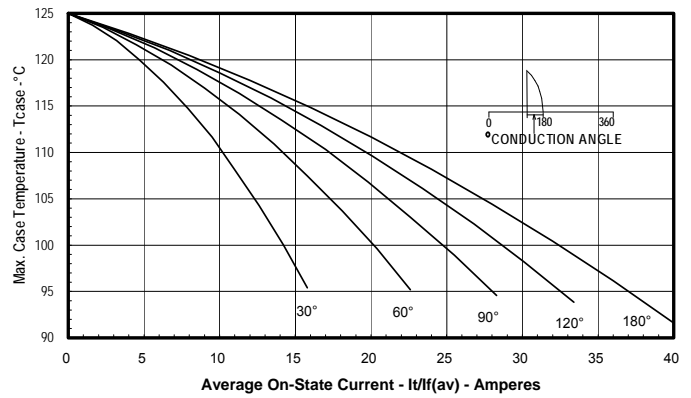
Maximum Transient Thermal Impedance
(Junction to Case)



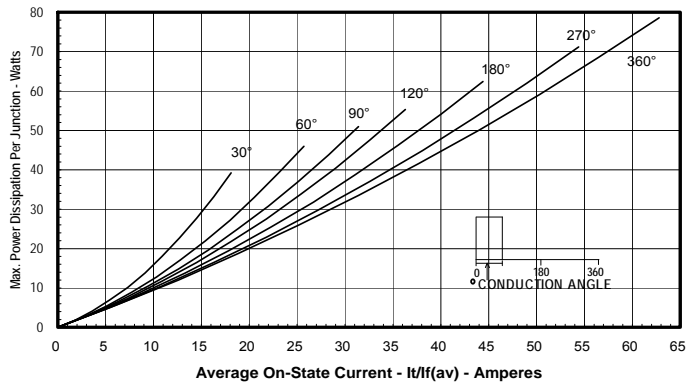
Maximum On-State Power Dissipation
(Sinusoidal Waveform)



Maximum Allowable Case Temperature
(Sinusoidal Waveform)



Maximum On-State Power Dissipation
(Rectangular Waveform)



Maximum Allowable Case Temperature
(Rectangular Waveform)

